

IN THE CLAIMS:

Please amend the claims as follows:

1. (Currently Amended) A method of manufacturing a crystal of a III-V compound of the nitride system comprising:
 - (a) growing a first crystal layer by growing a crystal of a III-V compound of the nitride system on a basal body;
 - (b) forming a first mask pattern on the first crystal layer;
 - (c) etching the first crystal layer through the first mask pattern;
 - (d) growing a second crystal layer by growing a crystal of a III-V compound of the nitride system from the first crystal layer;
 - (e) forming a second mask pattern on the second crystal layer; ~~and~~
 - (f) etching the second crystal layer through the second mask pattern;
 - (g) removing the second mask pattern to expose the second crystal layer; and
 - (h) growing a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer.

2. (Canceled)

3. (Previously Presented) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein the first mask pattern at least includes an under layer formed over the first crystal layer and an upper layer formed over the under layer.

4. (Previously Presented) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 3,

wherein the upper layer of the first mask pattern, and the second mask pattern are formed of a material which can be dissolved by a solution, and

the under layer of the first mask pattern is formed of a material which cannot be dissolved by the solution.

5. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein windows of the first mask pattern and windows of the second mask pattern do not overlie one another in the direction of the thickness of the crystal.

6. (Canceled)

7. (Previously Presented) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1, further comprising:

separating a portion of the crystal which includes at least the basal body, from the crystal, after the third growth step.

8. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein an inner layer is formed at least in one of the first crystal layer, the second crystal layer and the third crystal layer, and the inner layer has a different composition from the crystal layer in which the inner layer is formed.

9. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 8,

wherein the inner layer includes a III-V compound of the nitride system.

10. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes a plurality of pattern elements arranged in one direction in a plane almost parallel to the surface of the basal body.

11. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 10,

wherein both the pattern elements of the first mask pattern and the pattern elements of the second mask pattern are in the form of stripes.

12. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes pattern elements arranged in two directions in a plane almost parallel to the surface of the basal body.

13. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1,

wherein each of the first mask pattern and the second mask pattern includes silicon (Si) and at least one element selected from the group consisting of oxygen (O) and nitrogen (N).

14. (Original) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 13,

wherein the basal body comprises at least one of a sapphire (Al_2O_3), silicon (Si), silicon carbide (SiC), gallium arsenide (GaAs), magnesium aluminum composite oxide (MgAl_2O_4), lithium gallium composite dioxide (LiGaO_2) and gallium nitride (GaN).

15. (Currently Amended) A method of manufacturing a device, the method including a crystal growth step of forming a crystal substrate or a crystal film and comprising manufacturing a device by forming a device film over the crystal substrate or the crystal film,

wherein the crystal growth step comprises:

a first growth step of forming a first crystal layer by growing a crystal of a III-V compound of the nitride system on the surface of a basal body;

a first mask forming step of forming a first mask pattern on the surface of the first crystal layer;

a first etching step of etching the first crystal layer through the first mask pattern;

a second growth step of forming a second crystal layer by growing a crystal of a III-V compound of the nitride system from the first crystal layer;

a second mask forming step of forming a second mask pattern on the surface of the second crystal layer and ensuring that the second mask overlies a window in the first mask;

a second etching step of etching the second crystal layer through the second mask pattern;

and

a third growth step of forming a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer; and
between the second etching and the third growth step, a step of removing at least part of the second mask pattern.

16. (Original) A method of manufacturing a device as claimed in claim 15, further including a step of separating the basal body from the crystal substrate or the crystal film.

17. (Previously Presented) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1, further comprising:

growing a third crystal layer by growing a crystal of a III-V compound of the nitride system from the second crystal layer.

18. (Previously Presented) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 17, further comprising:

removing at least part of the second mask pattern after etching the second crystal layer but before growing the third crystal layer.

19. (Currently Amended) A method of manufacturing a crystal of a III-V compound of a nitride system comprising:

growing a first crystal layer of a III-V compound of the nitride system on a basal body;
forming a first mask pattern on the first crystal layer;
etching the first crystal layer through the first mask pattern; ~~and~~
growing a second crystal layer from the first crystal layer;

forming a second mask pattern on the second crystal layer;
etching the second crystal layer through the second mask pattern; and
forming a third crystal layer from the second crystal layer after removing at least a part
of the second mask layer.

20. (Previously Presented) The method of claim 19 further comprising forming a second mask pattern on the second crystal layer.

21. (Previously Presented) The method of claim 19 further comprising etching the second crystal layer through the second mask pattern.

22. (Previously Presented) The method of claim 21 further comprising growing a third crystal layer from the second crystal layer.

23. (New) A method of manufacturing a crystal of a III-V compound of the nitride system as claimed in claim 1, wherein the etching of the first crystal layer exposes the basal body.